

isc Silicon NPN Power Transistor

2N4910

DESCRIPTION

- Collector-Emitter Sustaining Voltage-  
:  $V_{CEO(SUS)} = 40V(\text{Min})$
- Low Collector Saturation Voltage-  
:  $V_{CE(sat)} = 0.6V(\text{Max.}) @ I_C = 1A$
- Wide Area of Safe Operation

APPLICATIONS

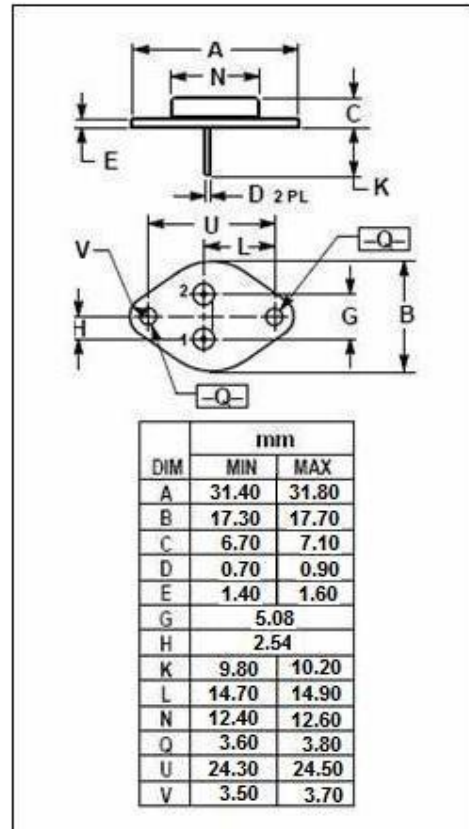
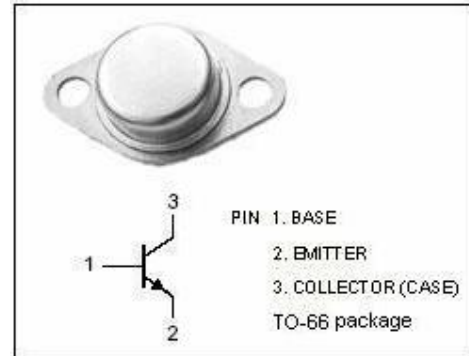
- Designed for driver circuits, switching and amplifier applications.

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	40	V
$V_{CEO}$	Collector-Emitter Voltage	40	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current-Continuous	1	A
$I_{CM}$	Collector Current-Peak	4	A
$I_B$	Collector Current-Continuous	1	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	25	W
$T_J$	Junction Temperature	200	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-65~200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	7.0	$^\circ\text{C/W}$



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## ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=100\text{mA}; I_B=0$	40			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=1\text{A}; I_B=0.1\text{A}$			0.6	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=1\text{A}; I_B=0.1\text{A}$			1.3	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=1\text{A}; V_{CE}=1\text{V}$			1.3	V
$I_{CEX}$	Collector Cutoff Current	$V_{CE}=40\text{V}; V_{BE(off)}=1.5\text{V}$ $V_{CE}=40\text{V}; V_{BE(off)}=1.5\text{V}; T_C=150^{\circ}\text{C}$			0.1 1.0	mA
$I_{CEO}$	Collector Cutoff Current	$V_{CE}=20\text{V}; I_B=0$			0.5	mA
$I_{CBO}$	Collector Cutoff Current	$V_{CB}=40\text{V}; I_E=0$			0.1	mA
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			1.0	mA
$h_{FE-1}$	DC Current Gain	$I_C=50\text{mA}; V_{CE}=1\text{V}$	40			
$h_{FE-2}$	DC Current Gain	$I_C=500\text{mA}; V_{CE}=1\text{V}$	20		100	
$h_{FE-3}$	DC Current Gain	$I_C=1\text{A}; V_{CE}=1\text{V}$	10			
$f_T$	Current-Gain—Bandwidth Product	$I_C=0.25\text{A}; V_{CE}=10\text{V}; f_{test}=1\text{MHz}$	3			MHz
$C_{OB}$	Output Capacitance	$I_E=0; V_{CB}=10\text{V}; f_{test}=100\text{kHz}$			100	pF